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PTO/SB/088 (08-03)

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Substitute for form 1449/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

Complete if Known

Application Number	10/716686
Filing Date	November 19, 2003
First Named Inventor	Bert M. VERMEIRE
Art Unit	Unknown 2829
Examiner Name	Unknown Arleen M. Vazquez
Attorney Docket Number	300-01-1-001

Sheet 1 of 2

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
AV	1	V. C. TYREE, "Self stressing test structure cells", Rome Laboratory, Air Force Materiel Command, February 1995, New York.	
AV	2	T. P. MA et al., "Ionizing Radiation Effects in MOS Devices and Circuits", John Wiley and Sons, 1989.	
AV	3	G. ANELLI et al., "Radiation tolerant VLSI circuits in standard deep submicron CMOS technologies for the LHC experiments: Practical design aspects," IEEE Trans. Nucl. Sci., vol. 46, pp. 1690-1696, 1999.	
AV	4	G. S. SHARE, "Effects of Ionizing Radiation on Thin Oxide (20- 1500 Å) MOS Capacitors," J. Appl. Phys., vol. 45, pp. 4894, 1974.	
AV	5	R. C. LACOE et al., "Total-dose radiation tolerance of a commercial 0.35 mm CMOS process," presented at Radiation Effects Data Workshop, 1998.	
AV	6	R. C. LACOE et al., "Total-dose tolerance of a Chartered Semiconductor 0.35 mm CMOS process," presented at Radiation Effects Data Workshop, 1999.	
AV	7	R. C. LACOE et al., "Application of Hardness-By-Design Methodology to Radiation-Tolerant ASIC Technologies," IEEE Trans. Nucl. Sci., vol. 47, pp. 2334-2341, 2000.	
AV	8	R. C. LACOE et al., "Total-dose tolerance of the commercial Taiwan Semiconductor Manufacturing Company (TSMC) 0.35 mm CMOS process," presented at Radiation Effects Data Workshop, 2001.	
AV	9	J. W. R. DAWES et al., "Process technology for radiation-hardened CMOS integrated circuits," IEEE J. Solid State Circuits, vol. SC-11, pp. 459, 1976.	
AV	10	J.M. BENEDETTO et al., "Mosfet and MOS Capacitor Responses to Ionizing Radiation" IEEE Transactions on Nuclear Science, Vol. NS-31, No. 6, Decemebr 1984.	

Examiner Signature	/Arleen Vazquez/	Date Considered	03/02/2007
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AV	11	A. MEKKAOUI et al., "30Mrad(SiO2) radiation tolerant pixel front end for the BTEV experiment," Nucl. Instr. and Meth. A, vol. 465, pp. 166-175, 2001.	
AV	12	J. D. M. FLEETWOOD, "A Reevaluation of Worst-Case Post-irradiation Response for Hardened MOS Transistors," IEEE Trans. Nucl. Sci., vol. NS-34, pp. 1178, 1987.	
AV	13	K. P. V. DRESSENDORFER, "The Effects of Test Conditions on MOS Radiation Hardness Results," IEEE Trans. Nucl. Sci., vol. NS-28, pp. 4281, 1981.	
AV	14	M. KIMURA, "Field and Temperature acceleration model for time-dependent dielectric breakdown," IEEE Trans. Electron Devices, vol. 46, pp. 220-229, 1999.	

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